



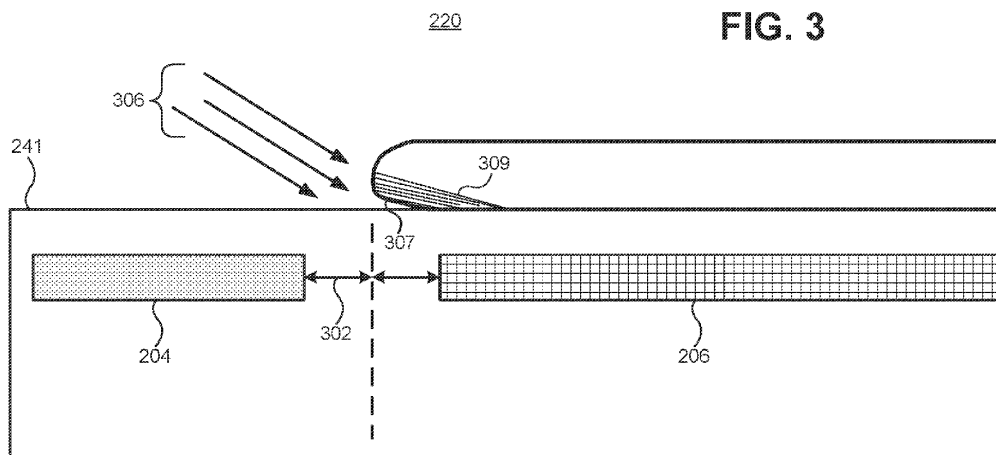
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(54) **Title:** ARC REDUCTION AND RF CONTROL FOR ELECTROSTATIC CHUCKS IN SEMICONDUCTOR PROCESSING



(57) **Abstract:** A semiconductor processing chamber may include a pedestal configured to support a substrate during a plasma-enhanced chemical-vapor deposition (PECVD) process that forms a film on a surface of the substrate. The chamber may also include one or more internal meshes embedded in the pedestal. The one or more internal meshes may be configured to deliver radio-frequency (RF) power to a plasma in the semiconductor processing chamber during the PECVD process. An outer diameter of the one or more internal meshes may be less than a diameter of the substrate. The chamber may further include an RF source configured to deliver the RF power to the one or more internal meshes. This configuration may reduce arcing within the processing chamber.

[Continued on next page]

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